

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

NVMFS6B03N

Power MOSFET

100 V, 4.8 mΩ, 145 A, Single N-Channel

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- NVMFS6B03NWF – Wettable Flank Option for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	100	V
Gate-to-Source Voltage	V_{GS}	± 16	V
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 3)	I_D	145	A
		102	
Power Dissipation $R_{\theta JC}$ (Notes 1, 2)	P_D	198	W
		99	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)	I_D	20	A
		14	
Power Dissipation $R_{\theta JA}$ (Notes 1 & 2)	P_D	3.9	W
		2.0	
Pulsed Drain Current	I_{DM}	520	A
Operating Junction and Storage Temperature	T_J, T_{stg}	-55 to + 175	°C
Source Current (Body Diode)	I_S	160	A
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}$, $V_{DD} = 50$ V, $V_{GS} = 10$ V, $I_{L(pk)} = 60$ A, $L = 0.1$ mH, $R_G = 25$ Ω)	E_{AS}	180	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State	$R_{\theta JC}$	0.76	°C/W
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	38	

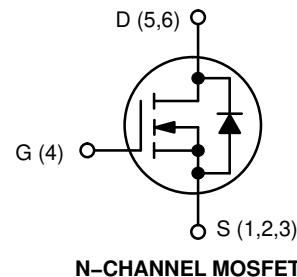
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



ON Semiconductor®

www.onsemi.com

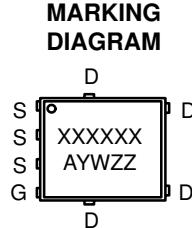
$V_{(BR)DSS}$	$R_{DS(ON) \text{ MAX}}$	$I_D \text{ MAX}$
100 V	4.8 mΩ @ 10 V	145 A



N-CHANNEL MOSFET



DFN5
(SO-8FL)
CASE 488AA
STYLE 1



MARKING
DIAGRAM

A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

NVMFS6B03N

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA		100			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			67.3			mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 80 V	T _J = 25°C		10		μA
			T _J = 125°C			100	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = 16 V			100		nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	2.0		4.0	V	
Negative Threshold Temperature Coefficient	V _{GS(TH)/T_J}			-8.1		mV/°C	
Drain-to-Source On Resistance	R _{DSS(on)}	V _{GS} = 10 V	I _D = 20 A		3.8	4.8	mΩ

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 50 V		4200		pF
Output Capacitance	C _{OSS}			760		
Reverse Transfer Capacitance	C _{RSS}			31		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 80 V; I _D = 50 A		58		nC
Threshold Gate Charge	Q _{G(TH)}			6.2		
Gate-to-Source Charge	Q _{GS}			19		
Gate-to-Drain Charge	Q _{GD}			17		
Plateau Voltage	V _{GP}			5.4		V
Gate Resistance	R _G	T _J = 25°C		1.0		Ω

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 10 V, V _{DS} = 80 V, I _D = 50 A, R _G = 1.0 Ω		16		ns
Rise Time	t _r			46		
Turn-Off Delay Time	t _{d(OFF)}			29		
Fall Time	t _f			11		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 50 A	T _J = 25°C		0.9	1.2	V
			T _J = 125°C		0.8		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 25 A			67		ns
Charge Time	t _a				35		
Discharge Time	t _b				31		
Reverse Recovery Charge	Q _{RR}				120		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

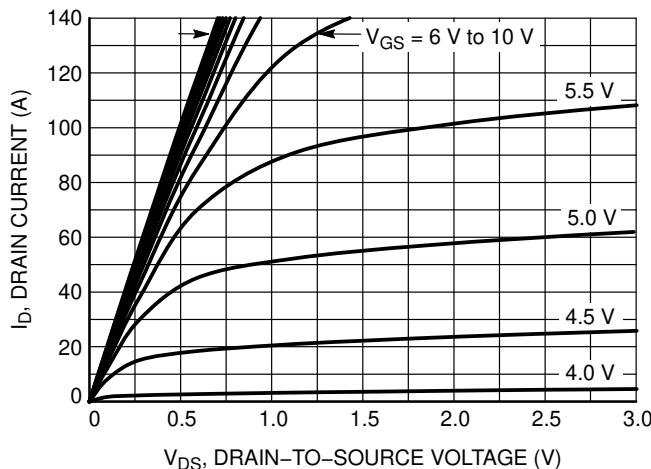


Figure 1. On-Region Characteristics

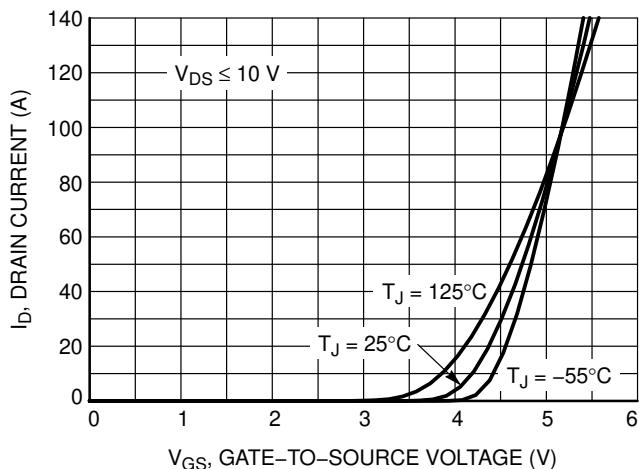


Figure 2. Transfer Characteristics

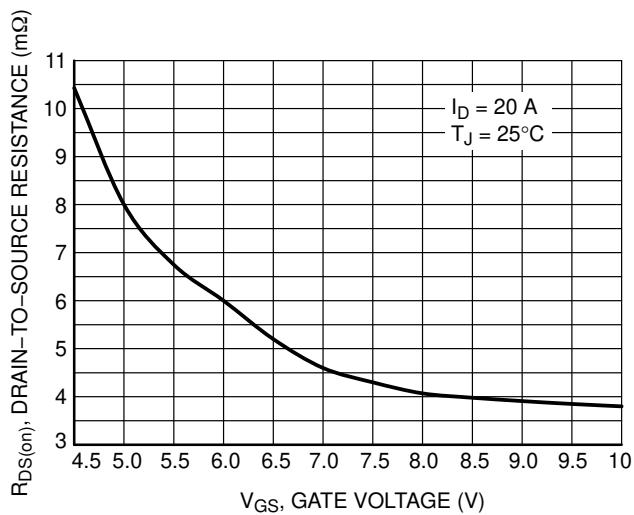


Figure 3. On-Resistance vs. Gate-to-Source Voltage

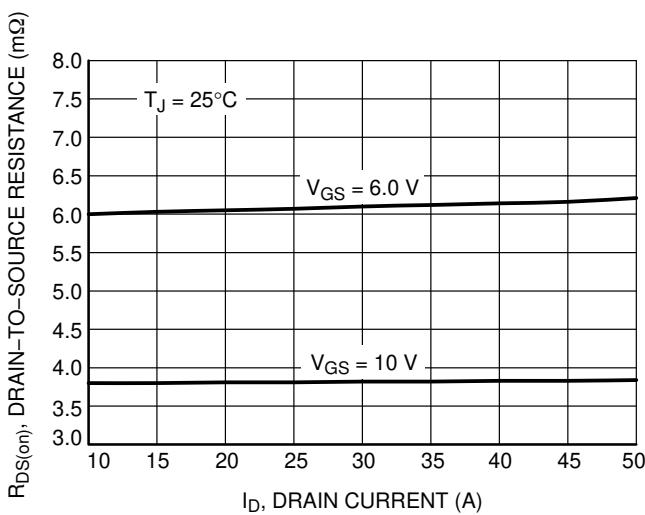


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

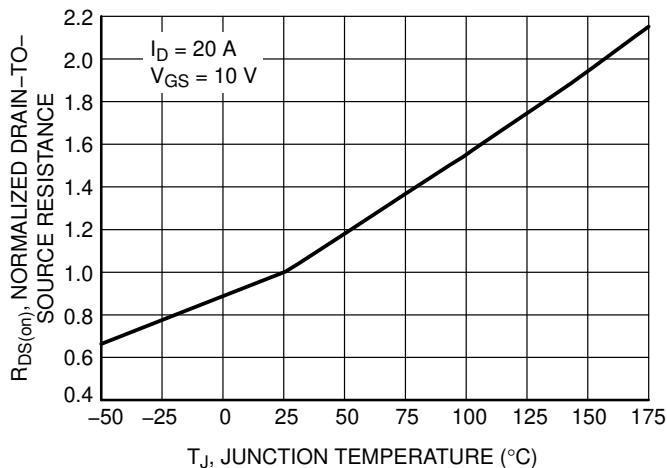


Figure 5. On-Resistance Variation with Temperature

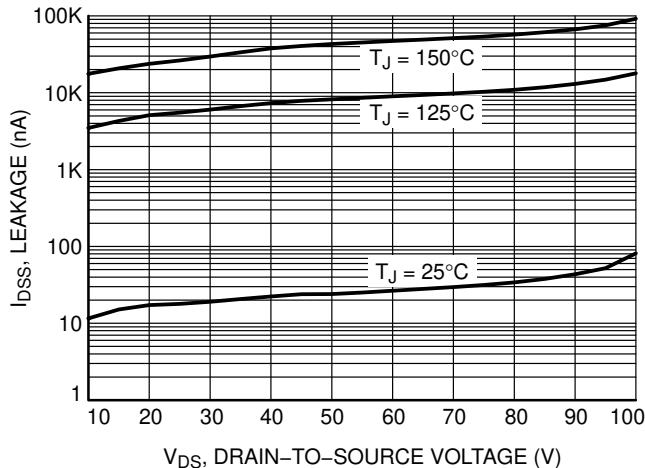


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

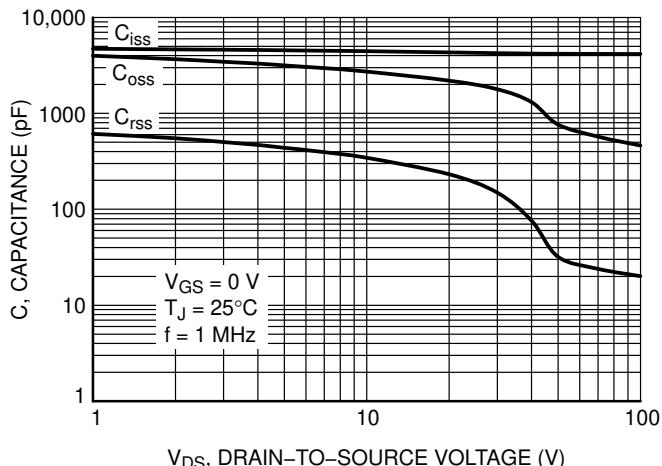


Figure 7. Capacitance Variation

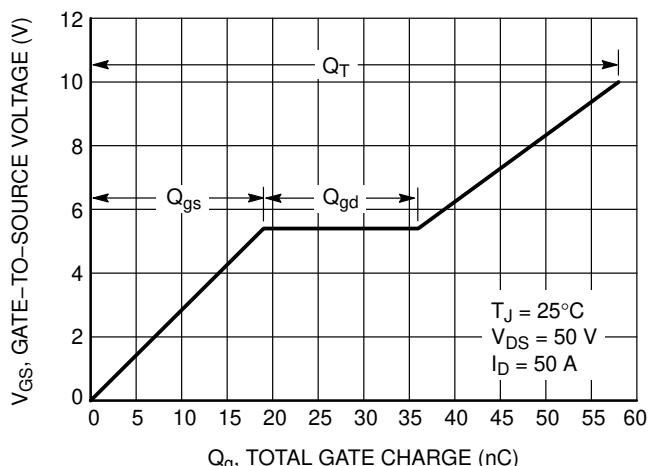


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

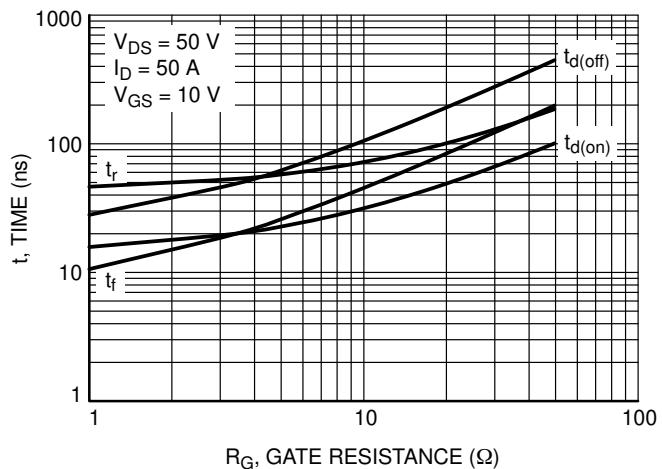


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

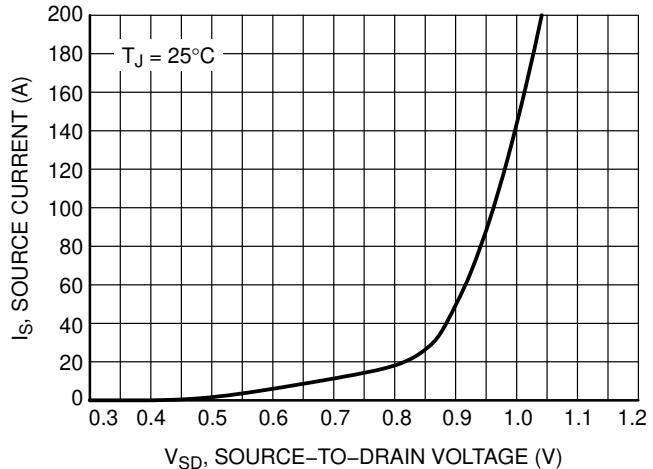


Figure 10. Diode Forward Voltage vs. Current

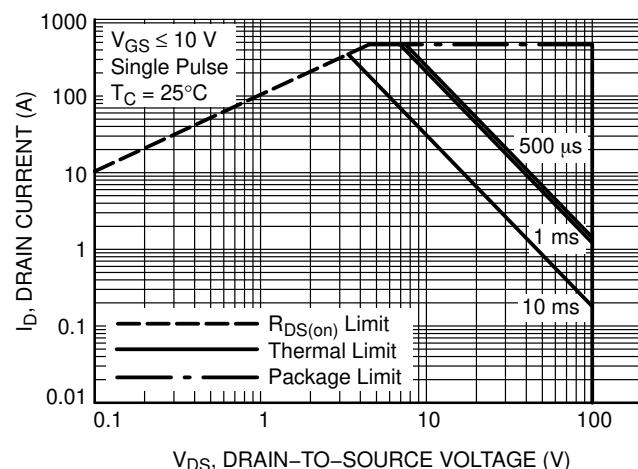


Figure 11. Maximum Rated Forward Biased Safe Operating Area

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TYPICAL CHARACTERISTICS

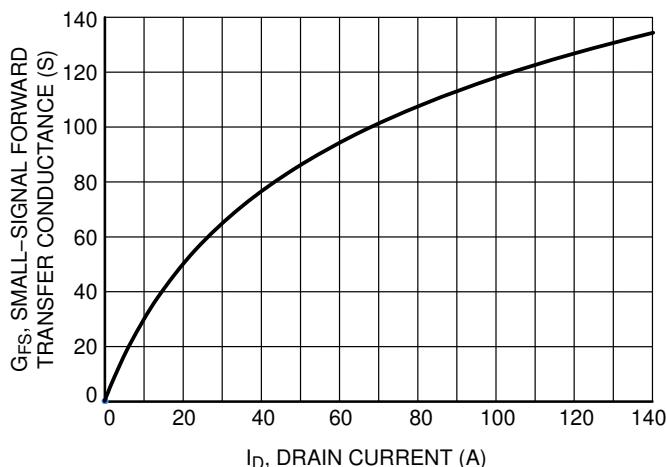


Figure 12. G_{FS} vs. I_D

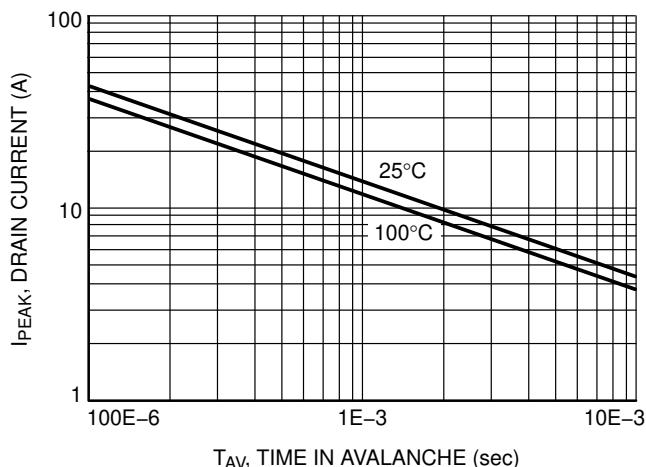


Figure 13. I_{PEAK} vs. T_{AV}

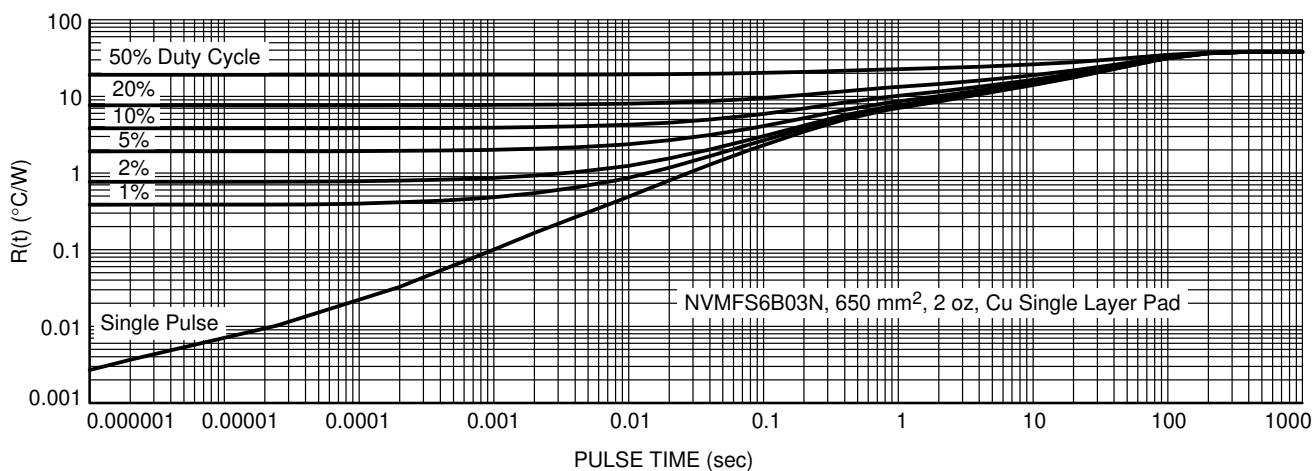


Figure 14. Thermal Response

DEVICE ORDERING INFORMATION

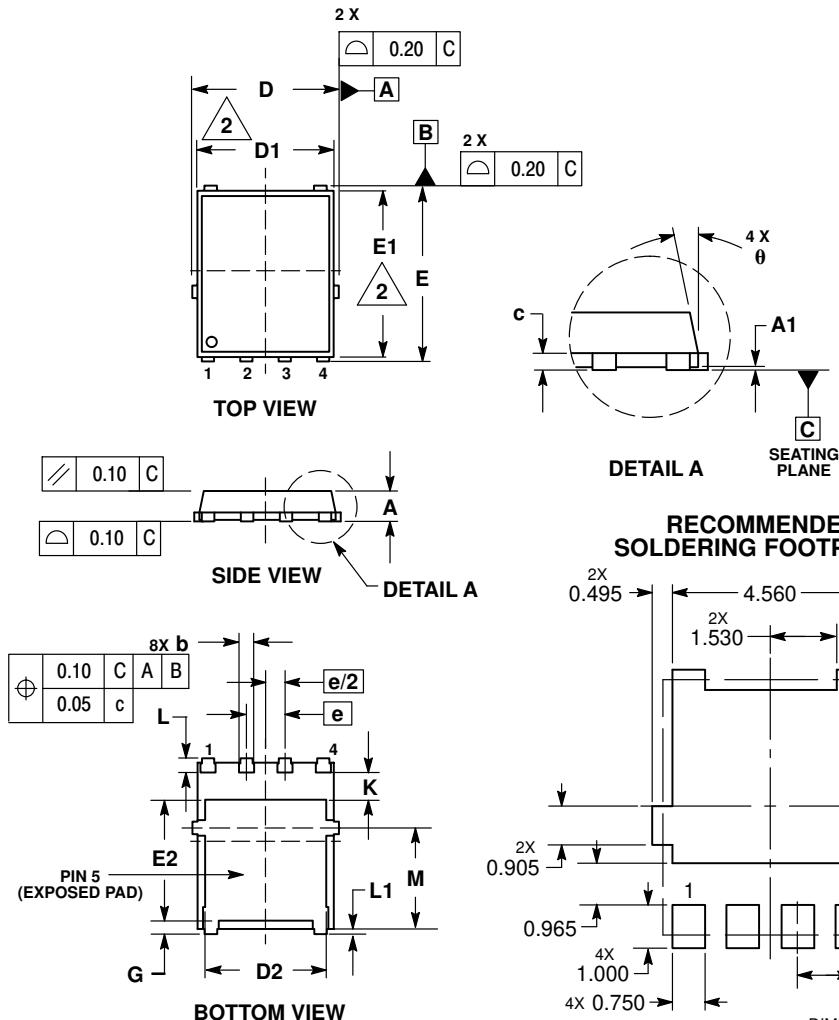
Device	Marking	Package	Shipping [†]
NVMFS6B03NT1G	6B03N	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS6B03NWFT1G	6B03WF	DFN5 (Pb-Free, Wettable Flanks)	1500 / Tape & Reel
NVMFS6B03NT3G	6B03	DFN5 (Pb-Free)	5000 / Tape & Reel
NVMFS6B03NWFT3G	6B03WF	DFN5 (Pb-Free, Wettable Flanks)	5000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NVMFS6B03N

PACKAGE DIMENSIONS

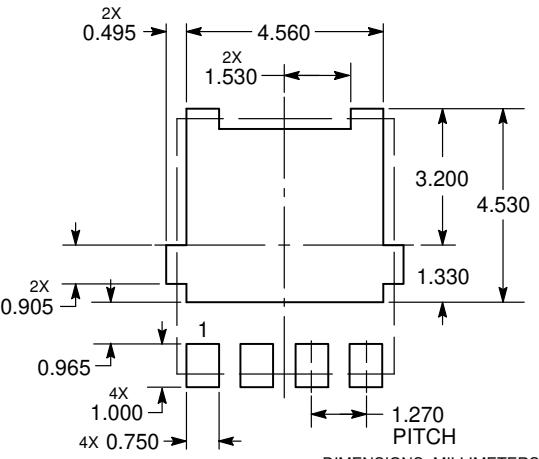
**DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE M**



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0 °	---	12 °

RECOMMENDED SOLDERING FOOTPRINT*



STYLE 1:
1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERMM/D.

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